SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995

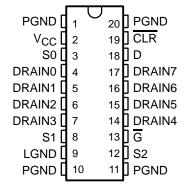
- Low r_{DS(on)} . . . 1.3 Ω Typical
- Avalanche Energy . . . 75 mJ
- Eight Power DMOS Transistor Outputs of 250-mA Continuous Current
- 1.5-A Pulsed Current Per Output
- Output Clamp Voltage at 45 V
- Four Distinct Function Modes
- Low Power Consumption

description

This power logic 8-bit addressable latch controls open-drain DMOS transistor outputs and is designed for general-purpose storage applications in digital systems. Specific uses include working registers, serial-holding registers, and decoders or demultiplexers. This is a multifunctional device capable of storing single-line data in eight addressable latches with 3-to-8 decoding or demultiplexing mode active-low DMOS outputs.

Four distinct modes of operation are selectable by controlling the clear (\overline{CLR}) and enable (\overline{G}) inputs as enumerated in the function table. In the addressable-latch mode, data at the data-in (D) terminal is written into the addressed latch. The addressed DMOS transistor output inverts the data input with all unaddressed DMOS-transistor outputs remaining in their previous states. In the memory mode, all DMOS-transistor outputs remain in their previous states and are unaffected by the data or address inputs. To eliminate the possibility of entering erroneous data in the latch, enable \overline{G} should be held high (inactive) while the address lines are changing. In the 3-to-8 decoding

DW OR N PACKAGE (TOP VIEW)



FUNCTION TABLE

INI	PUT	S	OUTPUT OF	EACH	FUNCTION
CLR	G	D	ADDRESSED DRAIN	OTHER DRAIN	FUNCTION
H H	L L	H L	L H	Q _{io} Q _{io}	Addressable Latch
Н	Н	Х	Q _{io}	Q _{io}	Memory
L L	L L	H L	L H	H H	8-Line Demultiplexer
L	Н	Х	Н	Н	Clear

LATCH SELECTION TABLE

SELE	CT IN	PUTS	DRAIN
S2	S1	S0	ADDRESSED
L	L	L	0
L	L	Н	1
L	Н	L	2
L	Н	Н	3
Н	L	L	4
Н	L	Н	5
Н	Н	L	6
Н	Н	Н	7

or demultiplexing mode, the addressed output is inverted with respect to the D input and all other outputs are high. In the clear mode, all outputs are high and unaffected by the address and data inputs.

Separate power and logic level ground pins are provided to facilitate maximum system flexibility. Pins 1, 10, 11, and 20 are internally connected, and each pin must be externally connected to the power system ground in order to minimize parasitic inductance. A single-point connection between pin 9, logic ground (LGND), and pins 1, 10, 11, and 20, power ground (PGND) must be externally made in a manner that reduces crosstalk between the logic and load circuits.

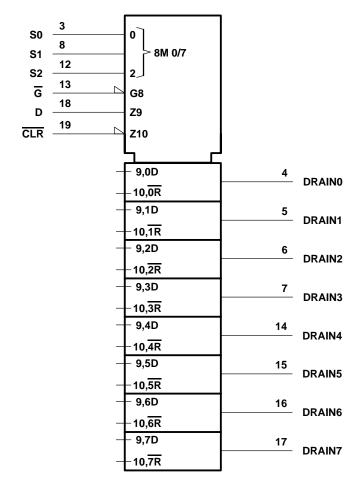
The TPIC6259 is characterized for operation over the operating case temperature range of -40° C to 125°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

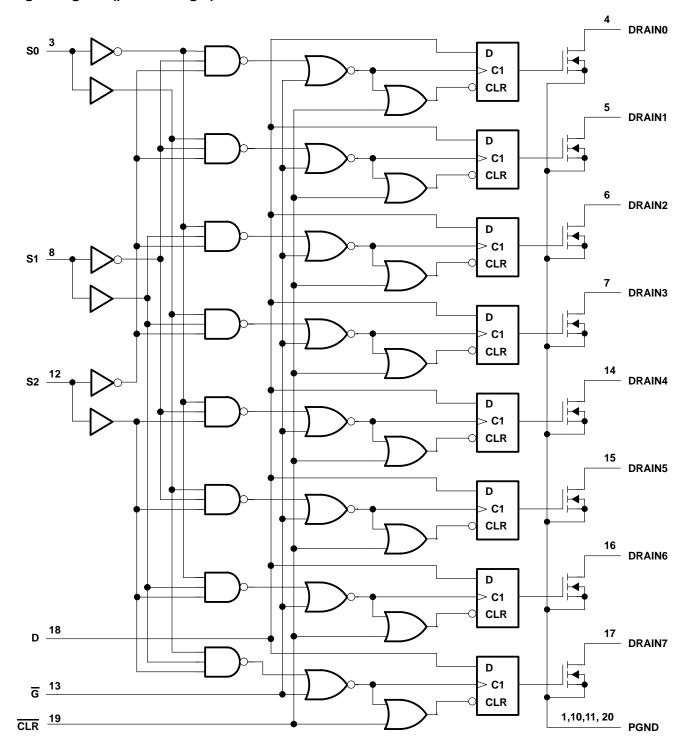


logic symbol†



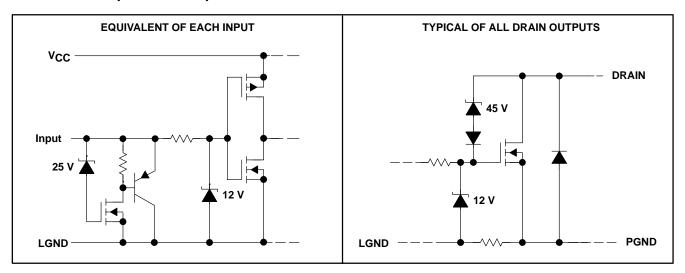
[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995

schematic of inputs and outputs



absolute maximum ratings over the recommended operating case temperature range (unless otherwise noted)†

Logic supply voltage, V _{CC} (see Note 1)	
Logic input voltage range, V _I	
Power DMOS drain-to-source voltage, V _{DS} (see Note 2)	45 V
Continuous source-drain diode anode current	1 A
Pulsed source-drain diode anode current	2 A
Pulsed drain current, each output, all outputs on, I_{Dn} , $T_A = 25^{\circ}C$ (see Note 3)	750 mA
Continuous drain current, each output, all outputs on, I_{Dn} , $T_A = 25$ °C	250 mA
Peak drain current single output, I _{DM} , T _A = 25°C (see Note 3)	
Single-pulse avalanche energy, E _{AS} (see Note 4)	
Avalanche current, I _{AS} (see Note 4)	
Continuous total power dissipation	See Dissipation Rating Table
Operating virtual junction temperature range, T _J	–40°C to 150°C
Storage temperature range, T _{stg}	
Lead temperature 1.6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values are with respect to LGND and PGND.
 - 2. Each power DMOS source is internally connected to PGND.
 - 3. Pulse duration \leq 100 μ s, duty cycle \leq 2%
 - 4. DRAIN supply voltage = 15 V, starting junction temperature, (TJS) = 25°C, L = 100 mH, IAS = 1 A (see Figure 4).

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{\scriptsize A}} \leq 25^{\circ}\mbox{\scriptsize C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 125°C POWER RATING
DW	1125 mW	9.0 mW/°C	225 mW
N	1150 mW	9.2 mW/°C	230 mW



SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995

recommended operating conditions over recommended operating temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Logic supply voltage, V _{CC}	4.5	5.5	V
High-level input voltage, V _{IH}	0.85 V _{CC}		V
Low-level input voltage, V _{IL}		0.15 V _{CC}	V
Pulsed drain output current, T _C = 25°C, V _{CC} = 5 V (see Notes 3 and 5)	-1.8	1.5	Α
Setup time, D high before $\overline{G} \uparrow$, t _{SU} (see Figure 2)	10		ns
Hold time, D high after \overline{G} ↑, t _h (see Figure 2)	5		ns
Pulse duration, t _W (see Figure 2)	15		ns
Operating case temperature, T _C	-40	125	°C

electrical characteristics, V_{CC} = 5 V, T_{C} = 25°C (unless otherwise noted)

	PARAMETER		TEST CONDITI	ONS	MIN	TYP	MAX	UNIT
V _{(BR)DSX}	Drain-source breakdown voltage	I _D = 1 mA			45			V
V_{SD}	Source-drain diode forward voltage	$I_F = 250 \text{ mA},$	See Note 3			0.85	1	V
lιΗ	High-level input current	$V_{CC} = 5.5 \text{ V},$	$V_I = V_{CC}$				1	μΑ
I _I L	Low-level input current	$V_{CC} = 5.5 \text{ V},$	V _I = 0				-1	μΑ
ICC	Logic supply current	I _O = 0,	All inputs low			15	100	μΑ
IN	Nominal current	V _{DS(on)} = 0.5 V _s See Notes 5, 6, a	$I_N = I_D$, and 7	T _C = 85°C,		250		mA
lnov	Off-state drain current	V _{DS} = 40 V				0.05	1	
IDSX	On-state drain current	V _{DS} = 40 V,	T _C = 125°C			0.15	5	μΑ
		I _D = 250 mA,	V _{CC} = 4.5 V			1.3	2	
rDS(on)	Static drain-source on-state resistance	I _D = 250 mA, V _{CC} = 4.5 V	T _C = 125°C,	See Notes 5 and 6 and Figures 8 and 9		2	3.2	Ω
		I _D = 500 mA,	V _{CC} = 4.5 V]		1.3	2	

switching characteristics, $V_{CC} = 5 \text{ V}$, $T_{C} = 25^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
tPLH	Propagation delay time, low-to-high-level output from D			625		ns	
tPHL	Propagation delay time, high-to-low-level output from D	$C_{\rm I} = 30 \rm pF,$ $I_{\rm D} = 250 \rm mA,$ 140				ns	
t _r	Rise time, drain output	See Figures 1, 2, and 10		650		ns	
t _f	Fall time, drain output			400		ns	
ta	Reverse-recovery-current rise time	I _F = 250 mA, di/dt = 20 A/μs,		100			
t _{rr}	Reverse-recovery time	See Notes 5 and 6 and Figure 3		300		ns	

NOTES: 3. Pulse duration $\leq 100 \,\mu\text{s}$, duty cycle $\leq 2\%$

- 5. Technique should limit $T_J T_C$ to 10°C maximum.
- 6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
- 7. Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at T_C = 85°C.

thermal resistance

	PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
D	DW package			111	°C AM	
$R_{\theta JA}$	Thermal resistance junction-to-ambient	N package	All 8 outputs with equal power		108	°C/W



PARAMETER MEASUREMENT INFORMATION

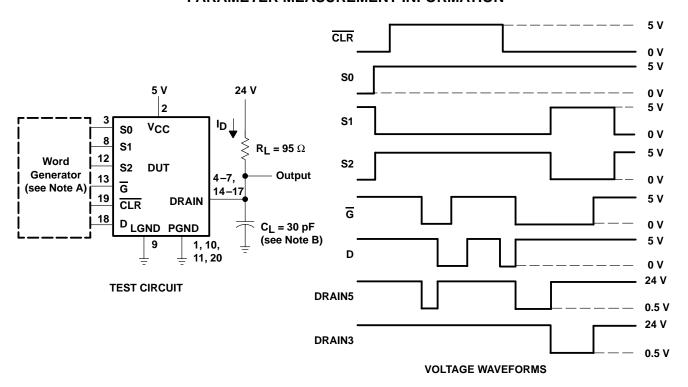


Figure 1. Typical Operation Mode

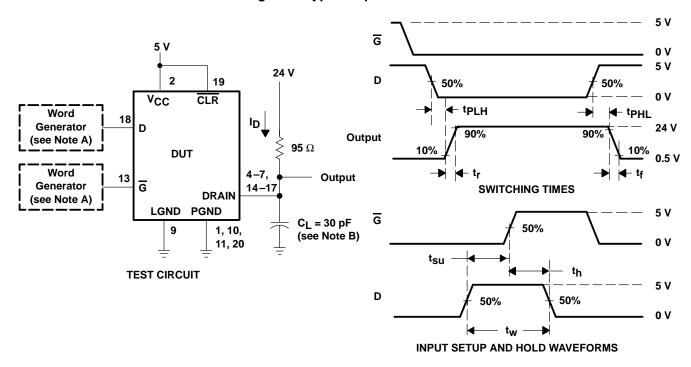


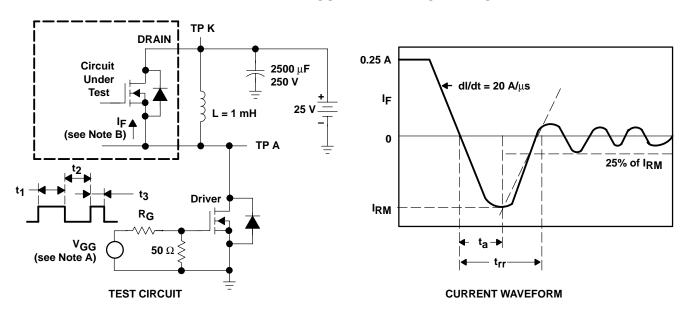
Figure 2. Test Circuit, Switching Times, and Voltage Waveforms

NOTES: A. The word generator has the following characteristics: $t_{\Gamma} \le 10$ ns, $t_{W} = 300$ ns, pulsed repetition rate (PRR) = 5 kHz, $Z_{O} = 50 \ \Omega$.

B. C_L includes probe and jig capacitance.

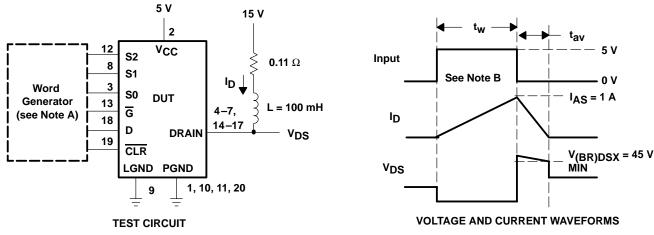


PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The VGG amplitude and RG are adjusted for di/dt = 20 A/ μ s. A VGG double-pulse train is used to set IF = 0.25 A, where t_1 = 10 μ s, t_2 = 7 μ s, and t_3 = 3 μ s.
 - B. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.

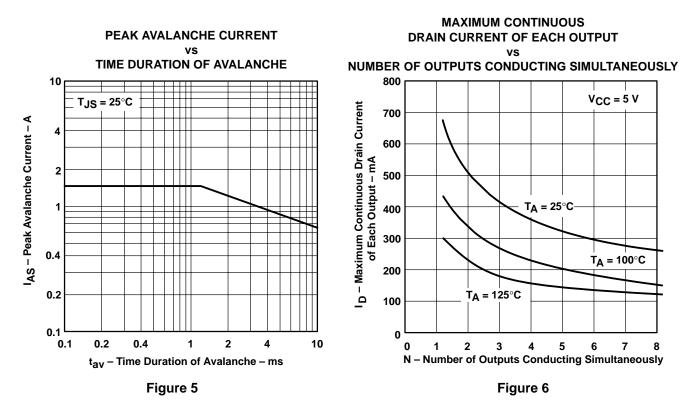
Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-Drain Diode



- NOTES: A. The pulse generator has the following characteristics: $t_r \le 10$ ns, $t_f \le 10$ ns, $z_0 = 50 \ \Omega$.
 - B. Input pulse duration, t_W , is increased until peak current $I_{AS} = 1$ A. Energy test level is defined as $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{av}/2 = 75$ mJ.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms

TYPICAL CHARACTERISTICS



MAXIMUM PEAK DRAIN CURRENT OF EACH OUTPUT vs

NUMBER OF OUTPUTS CONDUCTING SIMULTANEOUSLY

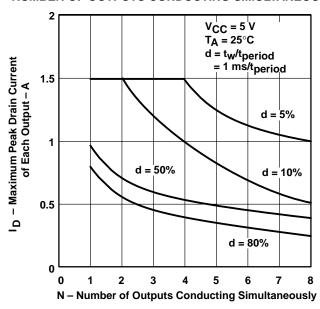
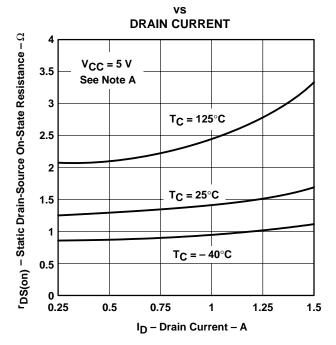


Figure 7

TYPICAL CHARACTERISTICS

STATIC DRAIN-SOURCE ON-STATE RESISTANCE



STATIC DRAIN-SOURCE ON-STATE RESISTANCE

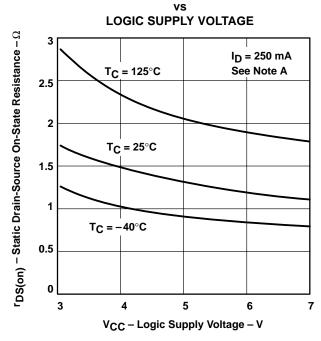


Figure 8 Figure 9

SWITCHING TIME

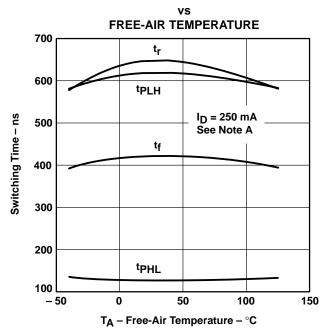


Figure 10

NOTE A: Technique should limit $T_J - T_C$ to 10°C maximum.







30-Apr-2012

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TPIC6259DW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6259DWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6259DWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6259DWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6259N	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

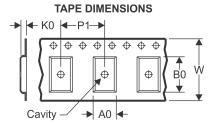
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 4-Jan-2013

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPIC6259DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1

PACKAGE MATERIALS INFORMATION

www.ti.com 4-Jan-2013



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPIC6259DWR	SOIC	DW	20	2000	367.0	367.0	45.0

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



DW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



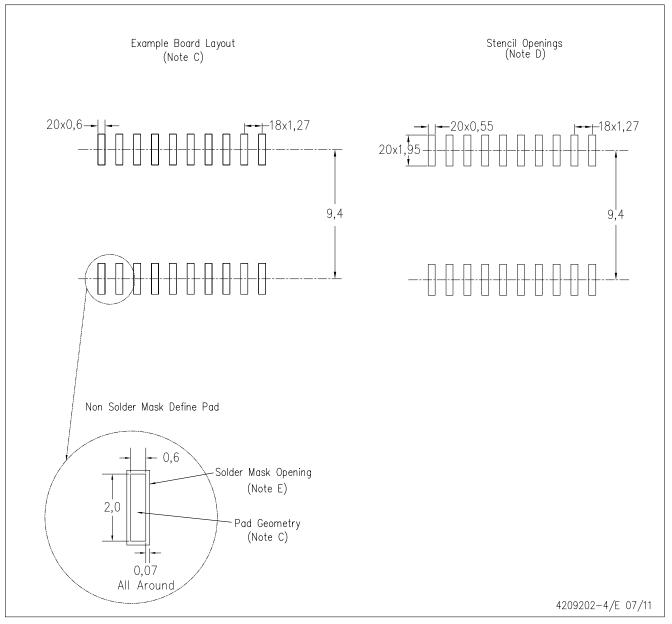
NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AC.



DW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC—7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products Applications

Audio www.ti.com/audio Automotive and Transportation www.ti.com/automotive Communications and Telecom **Amplifiers** amplifier.ti.com www.ti.com/communications **Data Converters** dataconverter.ti.com Computers and Peripherals www.ti.com/computers **DLP® Products** www.dlp.com Consumer Electronics www.ti.com/consumer-apps

DSP **Energy and Lighting** dsp.ti.com www.ti.com/energy Clocks and Timers www.ti.com/clocks Industrial www.ti.com/industrial Interface interface.ti.com Medical www.ti.com/medical logic.ti.com Logic Security www.ti.com/security

Power Mgmt power.ti.com Space, Avionics and Defense www.ti.com/space-avionics-defense

Microcontrollers <u>microcontroller.ti.com</u> Video and Imaging <u>www.ti.com/video</u>

RFID www.ti-rfid.com

OMAP Applications Processors www.ti.com/omap TI E2E Community e2e.ti.com

Wireless Connectivity <u>www.ti.com/wirelessconnectivity</u>